

ZXMN3A01F

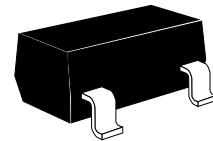
30V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = 30V$; $R_{DS(ON)} = 0.12\Omega$ $I_D = 2.0A$

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



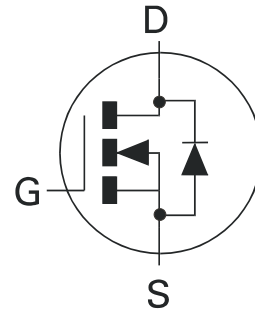
SOT23

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23 package

APPLICATIONS

- DC - DC Converters
- Power Management Functions
- Motor control

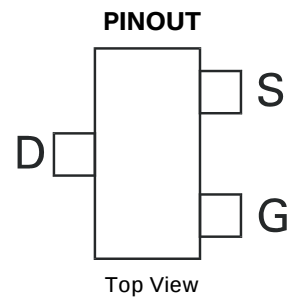


ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN3A01FTA	7"	8mm	3000 units
ZXMN3A01FTC	13"	8mm	10000 units

DEVICE MARKING

- 7N3



ZXMN3A01F

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS}=10V$; $T_A=25^\circ C$ (b) $V_{GS}=10V$; $T_A=70^\circ C$ (b) $V_{GS}=10V$; $T_A=25^\circ C$ (a)	I_D	2.0 1.6 1.8	A
Pulsed Drain Current (c)	I_{DM}	8	A
Continuous Source Current (Body Diode) (b)	I_S	1.3	A
Pulsed Source Current (Body Diode) (c)	I_{SM}	8	A
Power Dissipation at $T_A=25^\circ C$ (a) Linear Derating Factor	P_D	625 5	mW mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b) Linear Derating Factor	P_D	806 6.4	mW mW/ $^\circ C$
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150	$^\circ C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	200	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	155	$^\circ C/W$

NOTES

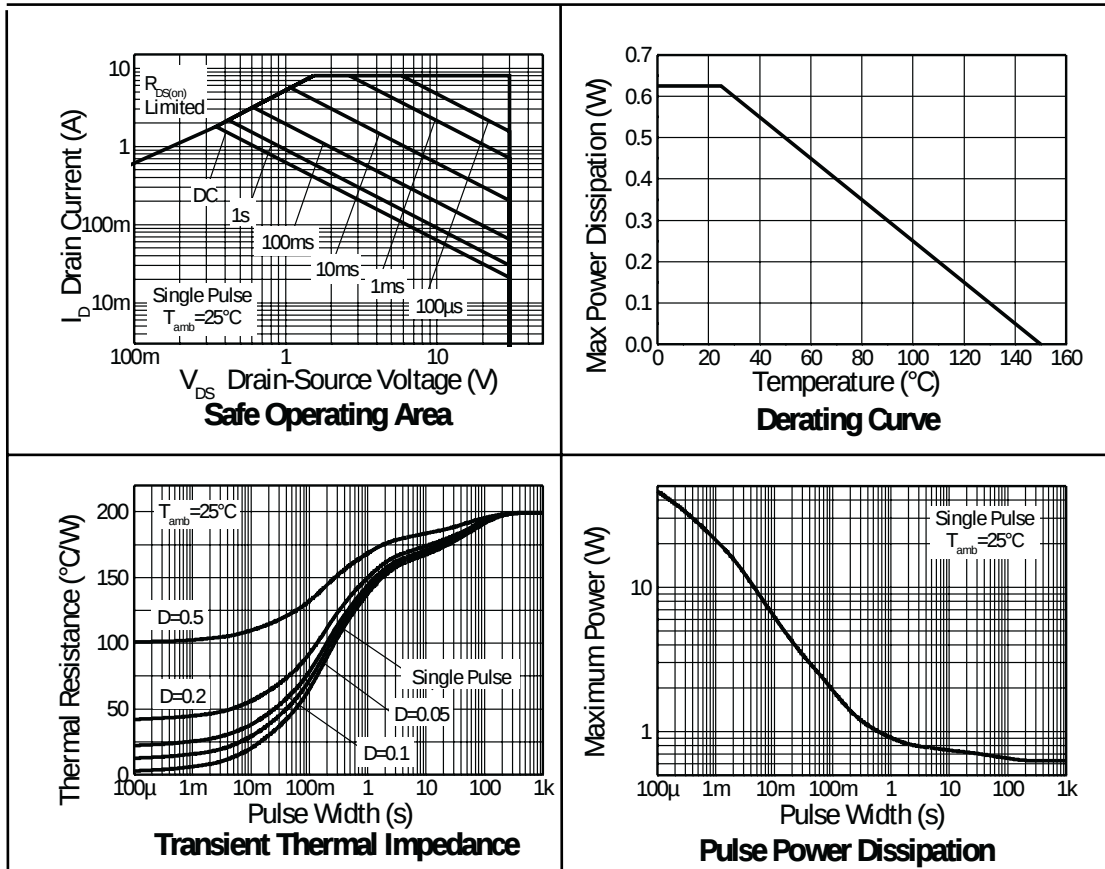
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.05$, pulse width $10\mu s$ - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

ZXMN3A01F

CHARACTERISTICS



ZXMN3A01F

ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise stated).

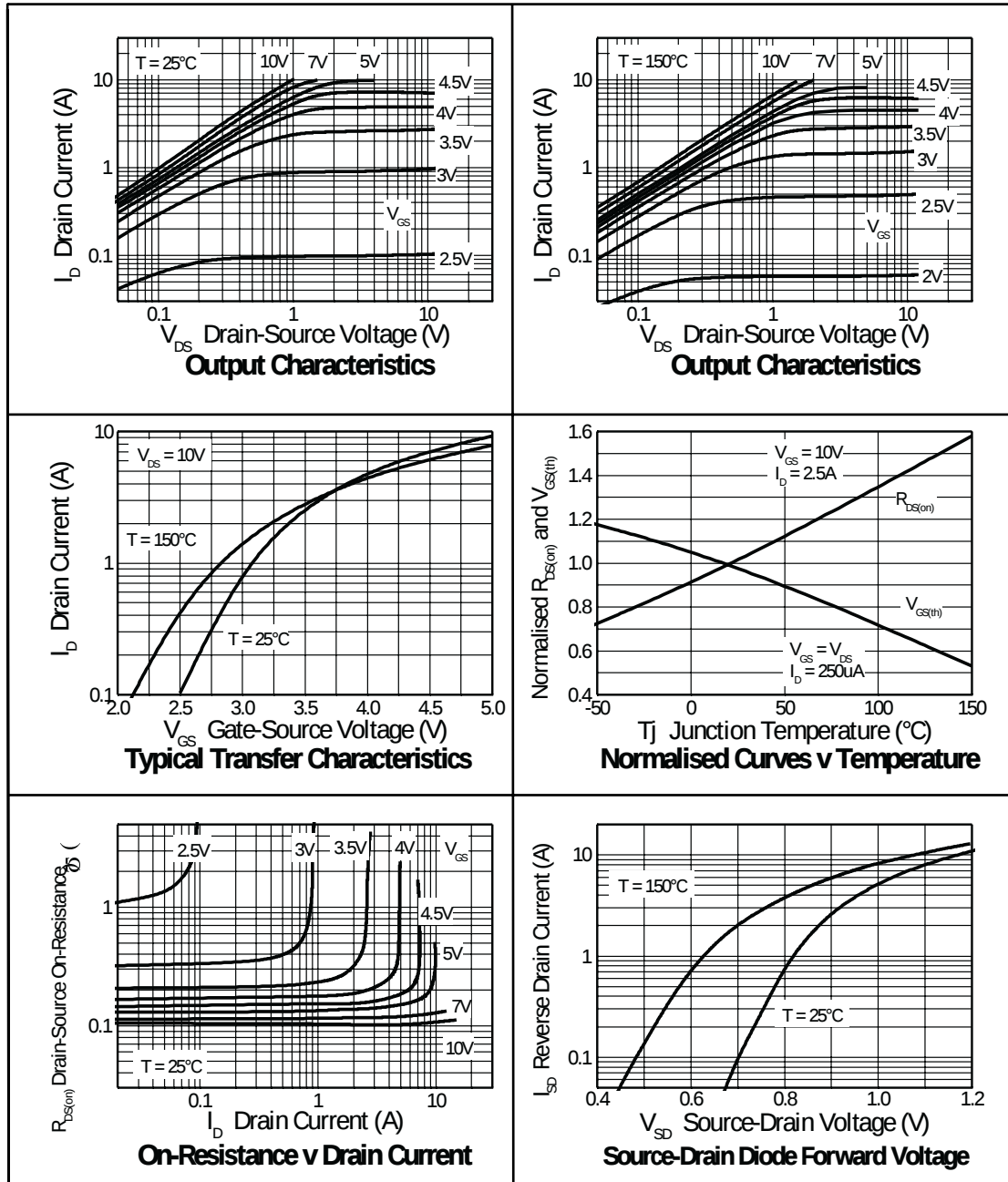
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	30			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			0.5	μA	V _{DS} =30V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	1			V	I _D =250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}		0.106	0.12 0.18	Ω Ω	V _{GS} =10V, I _D =2.5A V _{GS} =4.5V, I _D =2.0A
Forward Transconductance (1)(3)	g _{fs}		3.5		S	V _{DS} =4.5V,I _D =2.5A
DYNAMIC (3)						
Input Capacitance	C _{iss}		190		pF	V _{DS} =25 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		38		pF	
Reverse Transfer Capacitance	C _{rss}		20		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		1.7		ns	V _{DD} =15V, I _D =2.5A R _G ≅6.0Ω, V _{GS} =10V
Rise Time	t _r		2.3		ns	
Turn-Off Delay Time	t _{d(off)}		6.6		ns	
Fall Time	t _f		2.9		ns	
Gate Charge	Q _g		2.3		nC	V _{DS} =15V,V _{GS} =5V, I _D =2.5A
Total Gate Charge	Q _g		3.9		nC	V _{DS} =15V,V _{GS} =10V, I _D =2.5A
Gate-Source Charge	Q _{gs}		0.6		nC	
Gate-Drain Charge	Q _{gd}		0.9		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}		0.85	0.95	V	T _J =25°C, I _S =1.7A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		17.7		ns	T _J =25°C, I _F =2.5A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Q _{rr}		13.0		nC	

NOTES

- (1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

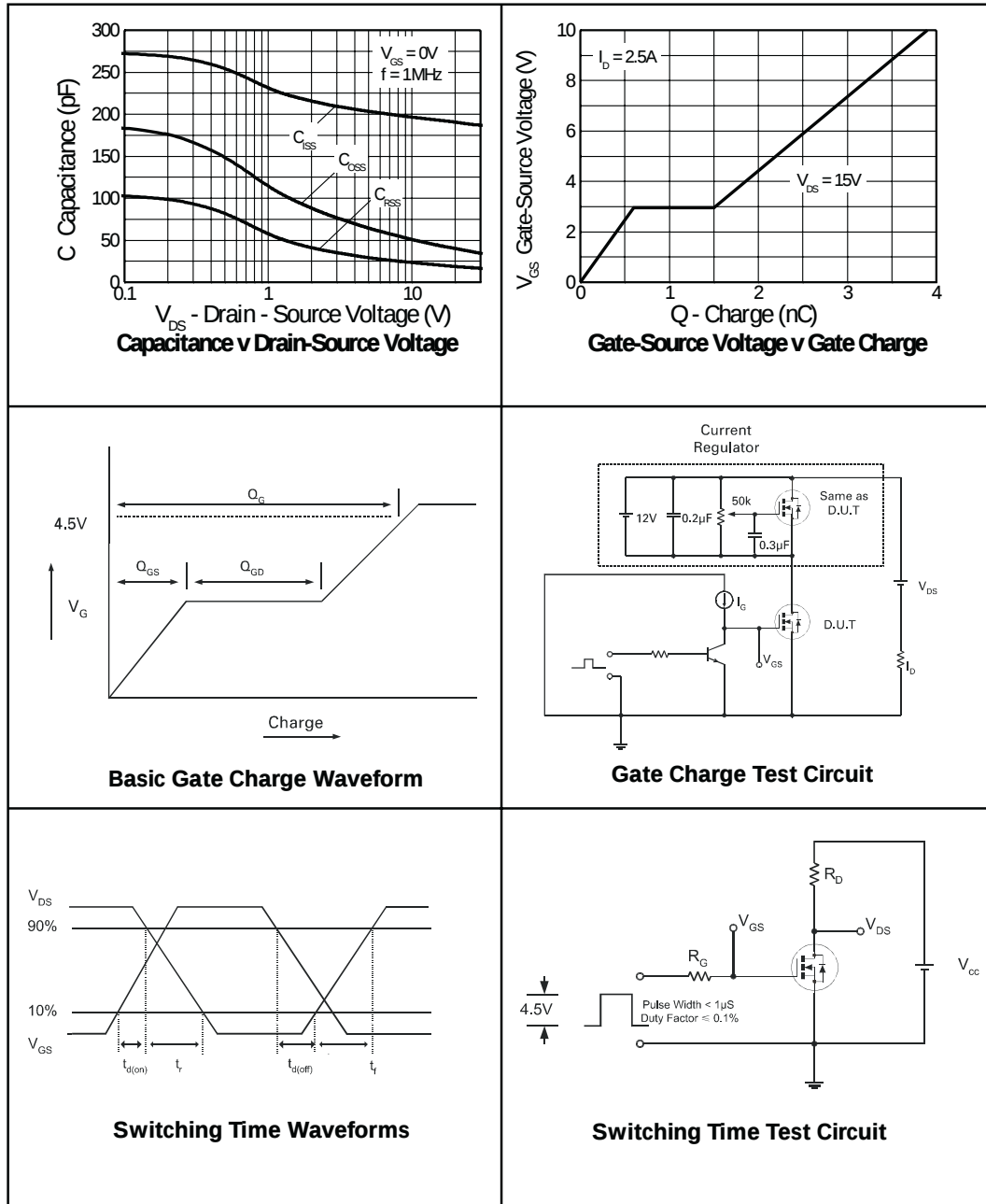
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TYPICAL CHARACTERISTICS



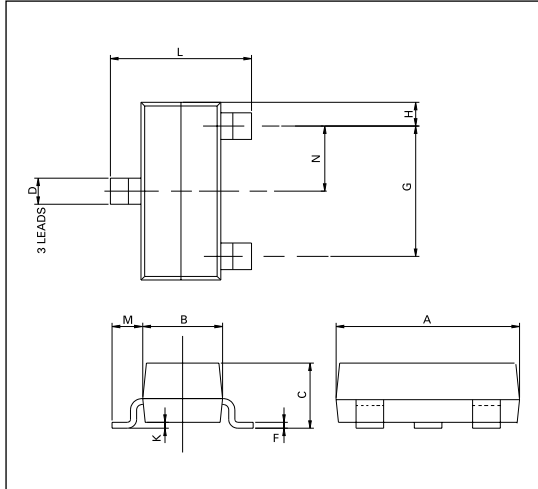
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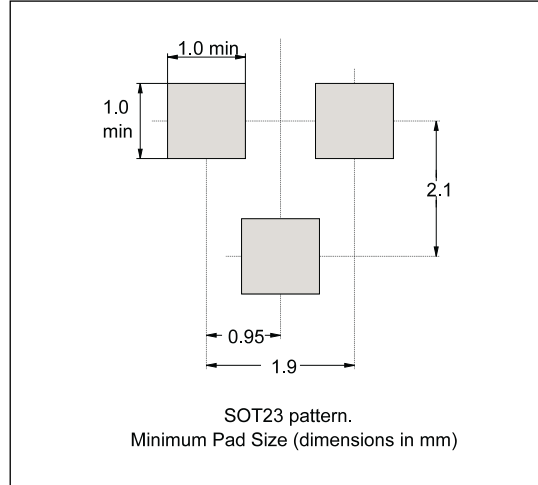


ZXMN3A01F

PACKAGE OUTLINE



PAD LAYOUT



CONTROLLING DIMENSIONS IN MILLIMETRES APPROX CONVERSIONS INCHES.

PACKAGE DIMENSIONS

DIM	MILLIMETRES		INCHES		DIM	MILLIMETRES		INCHES	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	—	1.10	—	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		φ	10° TYP		10° TYP	

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